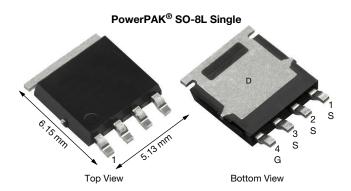


www.vishay.com

Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0140			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0200			
I _D (A)	-30			
Configuration	Single			
Package	PowerPAK SO-8L			

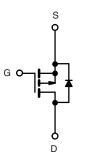
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V_{DS}	-40	V	
Gate-source voltage		V_{GS}	± 20		
Continuous drain current	T _C = 25 °C ^a	ı	-30		
	T _C = 125 °C	l _D	-23		
Continuous source current (diode conduction) ^a		I _S	-30	Α	
Pulsed drain current ^b		I _{DM}	-120		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	-25		
Single pulse avalanche energy	L = 0.1 MH	E _{AS}	31.2	mJ	
Maximum power dissipation ^b	T _C = 25 °C	Б	45	W	
	T _C = 125 °C	P_{D}	15		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) d, e			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	70	°C/W
unction-to-case (drain)		R_{thJC}	3.3	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishay.com/doc?73257). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0$, $I_D = -250 \mu A$		-40	-	-	.,
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-1.5	-2.0	-2.5	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
Zero gate voltage drain current		V _{GS} = 0 V	V V _{DS} = -40 V		-	-1	
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 125 °C	-	-	-50	μΑ
		$V_{GS} = 0 V$	V _{DS} = -40 V, T _J = 175 °C	-	-	-150	
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \ge -5 \text{ V}$	-30	-	-	Α
Drain-source on-state resistance ^a	, ,	V _{GS} = -10 V	I _D = -10 A	-	0.0115	0.0140	Ω
		V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0219	
	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	-	-	0.0261	
		V _{GS} = -4.5 V		-	0.0163	0.0200	
Forward transconductance b	9 _{fs}	V _{DS} =	-15 V, I _D = -10 A	-	37	-	S
Dynamic ^b						L	
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = -25 V, f = 1 MHz	-	4405	6000	pF
Output capacitance	C _{oss}			-	248	350	
Reverse transfer capacitance	C _{rss}			-	234	320	
Total gate charge ^c	Q_{g}			-	63	95	
Gate-source charge c	Q _{gs}	V _{GS} = -10 V	$V_{GS} = -10 \text{ V}$ $V_{DS} = -20 \text{ V}, I_D = -2.5 \text{ A}$		9.5	-	nC
Gate-drain charge ^c	Q _{gd}				9.5	-	
Gate resistance	R _g	f = 1 MHz		2	4.6	7	Ω
Turn-on delay time ^c	t _{d(on)}	$V_{DD} = \text{-20 V, R}_L = 8 \ \Omega$ $I_D \cong \text{-2.5 A, V}_{GEN} = \text{-10 V, R}_g = 1 \ \Omega$		-	12	20	ns
Rise time ^c	t _r			-	4	10	
Turn-off delay time ^c	t _{d(off)}			-	67	110	
Fall time ^c	t _f			-	17	30	
Source-Drain Diode Ratings and Chara	acteristics ^b				•		
Pulsed current a	I _{SM}			-	-	-120	Α
Forward voltage	V _{SD}	I _F = -10 A, V _{GS} = 0 V		-	-0.82	-1.2	V
Body diode reverse recovery time	t _{rr}	I _F = -2.5 A, di/dt = 100 A/μs		-	26	55	ns
Body diode reverse recovery charge	Q _{rr}			-	21	50	nC
Reverse recovery fall time	ta			-	15	-	ns
Reverse recovery rise time	t _b			-	11	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.6	-	Α

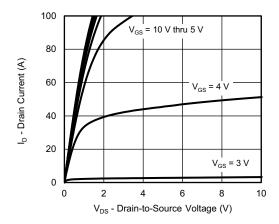
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

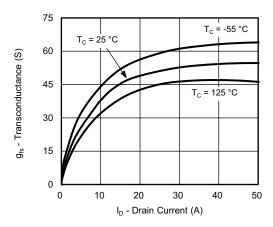
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



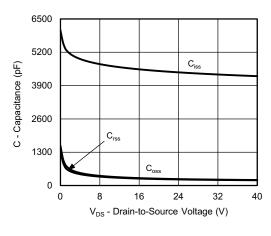
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



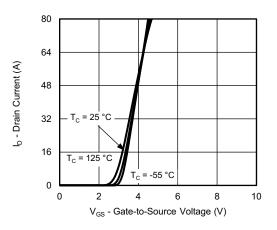
Output Characteristics



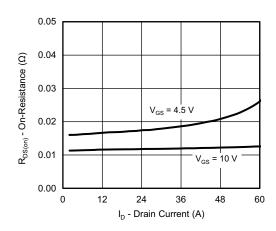
Transconductance



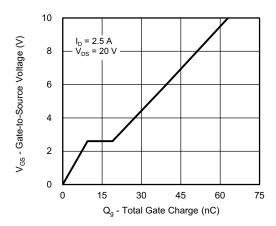
Capacitance



Transfer Characteristics



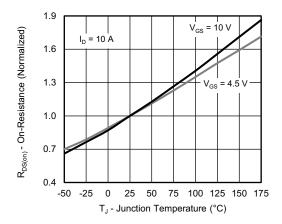
On-Resistance vs. Drain Current



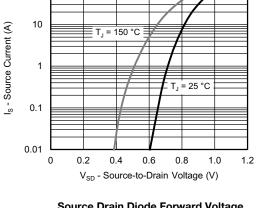
Gate Charge



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

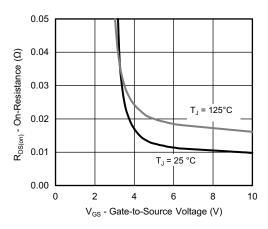


On-Resistance vs. Junction Temperature

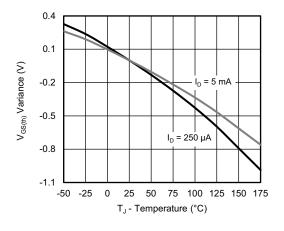


100

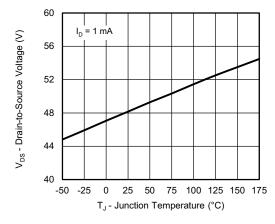
Source Drain Diode Forward Voltage



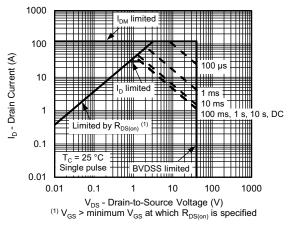
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



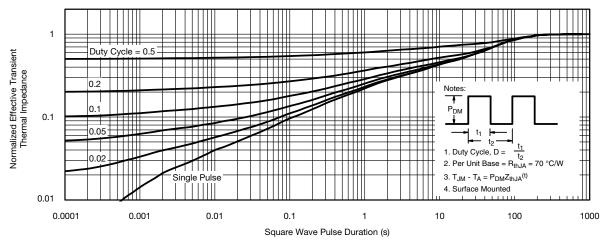
Drain-Source Breakdown vs. Junction Temperature



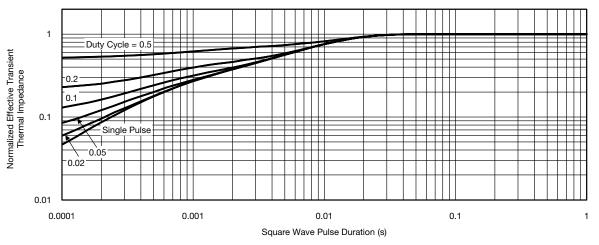
Safe Operating Area



THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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